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Metal	
Overall Length:	
1.253 inches	
Overall Diamete	
0.505 inches	•
Mounting Facili	v Quantity
1	
	Device Engineering Council/jedec/case Outline Designation:
Do-4	
	ally-electrically Connected To Case:
Anode	
Mounting Metho	d:
Threaded stud	
Overall Width A	ross Flats:
Between 0.423 ir	ches and 0.438 inches
Thread Size:	
0.190 inches	
Semiconductor	Material:
Silicon	
Voltage Rating	n Volts Per Characteristic:
39.0 regulator v	
Voltage Toleran	-
-5.0/+5.0	
Current Rating	er Characteristic:
-	es repetitive peak forward current
-	r Characteristic:
- 10.0 watts small-	signal input power, common-collector preset
Maximum Opera	ting Tempurature Per Measurement Point:
175.0 degrees ce	Isius junction
Precious Materi	Il And Location:
Lead finish option	silver or gold
Precious Materi	d:
Gold or silver	
Test Data Docu	nent:
81349-mil-s-1950	0 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specificatior
format; excludes	commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental ar	d performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series D	esignator:
Unf	
Terminal Type A	nd Quantity:
	and 1 threaded stud
Specification Da	
	0/124 government specification

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

